Abstracts

Experimental Gain and Noise Parameters of Microwave GaAs FET's in the L and S Bands (Short Papers)

A. Anastassiou and M.J.O. Strutt. "Experimental Gain and Noise Parameters of Microwave GaAs FET's in the L and S Bands (Short Papers)." 1973 Transactions on Microwave Theory and Techniques 21.6 (Jun. 1973 [T-MTT]): 419-422.

The design of microwave amplifiers with GaAs FET's assumes the knowledge of the four gain and the four noise parameters as a function of the biasing conditions. The gain parameters at three different bias conditions have been calculated by computer from the measured scattering parameters. The noise figures as a function of the same bias conditions have also been measured. The four fundamental noise parameters have been determined. The GaAs FET's are units from Plessey (England). At present, these are the only units which are commercially available.

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